

IN THE SPECIFICATION

Please insert the following paragraph at page 1, between lines 2 and 3 (i.e., after the title):

This application is a divisional application of allowed parent application Serial No. 09/401,849, filed on September 22, 1999, which claims benefit of priority under 35 U.S.C. § 119 to Japanese Patent Application No. 11-141271, filed on May 21, 1999, the entire contents of which is incorporated by reference herein.

Please amend the specification at page 21, lines 6-11 to read as follows:

FIG. 19 is a sectional view showing the structure of an MOSFET according to a second preferred embodiment of the present invention. As shown in FIG. 19, on the basis of the MOSFET of the first preferred embodiment shown in FIG. 1, the MOSFET of the second preferred embodiment has a gate insulating film 25 made of a material having a larger dielectric constant than the silicon oxide film 5. The gate insulating film 25 in Figure 19 is used in place of the gate insulating film 7 (see Figure 14, for example) made of silicon oxide film.